

Supplementary information

Pulsed chemical vapour deposition of conformal GeSe for application as OTS selector

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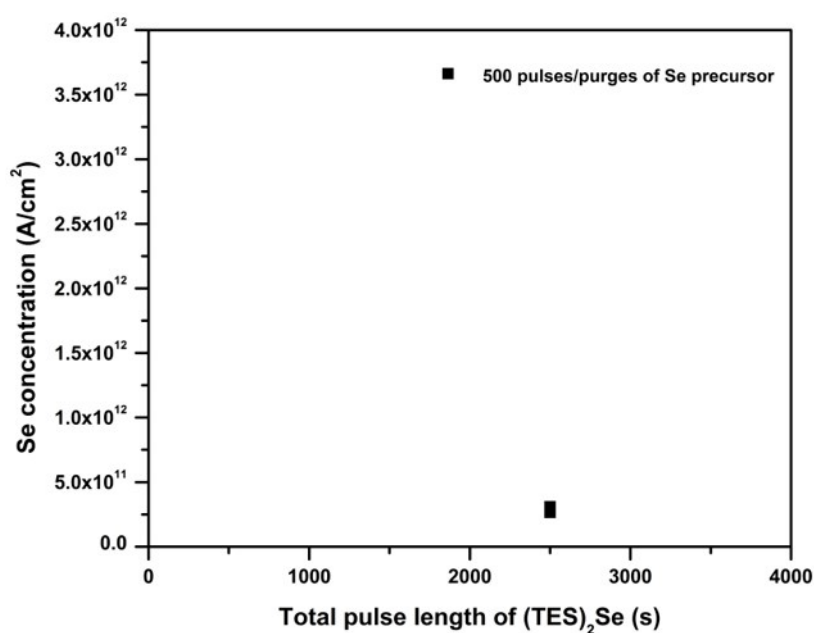


Figure S1: Se concentration vs total pulse length of (TES)₂Se on Si substrate: no Se chemisorption occurred on Si substrate.

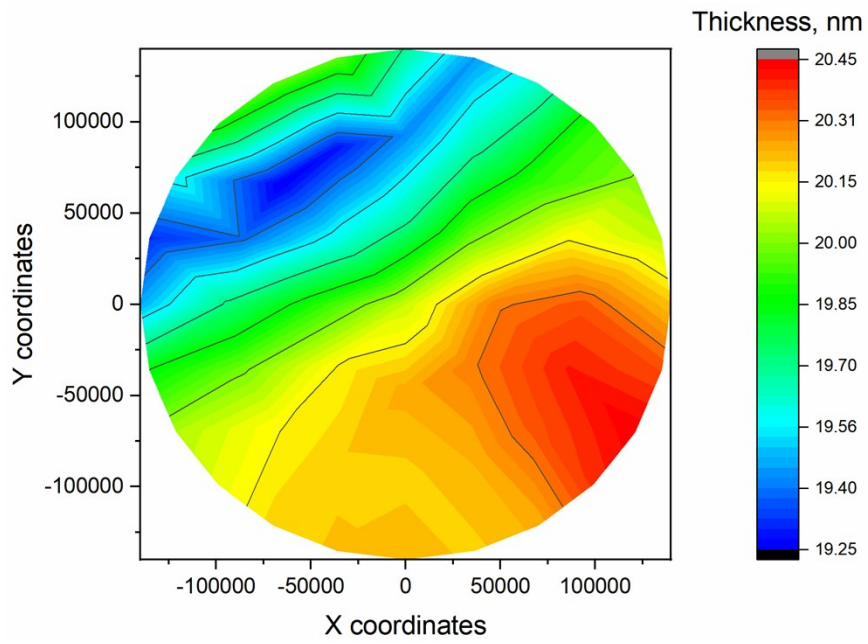


Figure S2: Ellipsometer contour map revealing the thickness uniformity of GeSe across 300 mm wafer

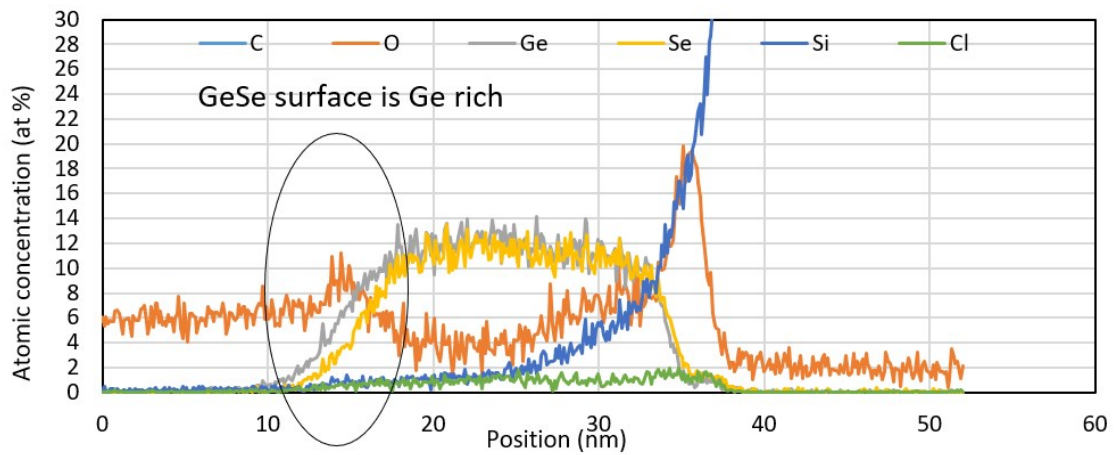


Figure S3: EDS line scan of GeSe sample across air-GeSe interface to GeSe-Si interface.